

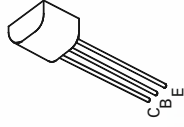
NPN SILICON PLANAR R.F. MEDIUM POWER TRANSISTOR

ZTX3866

ISSUE 2 – MARCH 94

FEATURES

- * 1W P_{OUT} at 175 MHz, 28V, 18dB typical
- * 1W P_{OUT} at 400 MHz, 28V, 9.7dB typical
- * High P_{tot}
- * High efficiency



E-Line
TO92 Compatible

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ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	55	V
Collector-Emitter Voltage	V_{CEO}	30	V
Collector-Emmitter Voltage	V_{CER}	55	V
Emitter-Base Voltage	V_{EBO}	3.5	V
Continuous Collector Current	I_{CM}	400	mA
Power Dissipation	P_{tot}	350	mW
Operating and Storage Temperature Range	T_j, T_{stg}	-55 to +175	$^{\circ}C$

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$ unless otherwise stated).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	55			V	$I_C = 100\mu A, I_E = 0$
Collector-Emmitter Breakdown Voltage	$V_{(BR)CEO(sus)}$	30			V	$I_C = 5mA, I_B = 0$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	3.5			V	$I_E = 100\mu A, I_C = 0$
Collector-Emitter Cut-Off Current	I_{CEO}			20	μA	$V_{CB} = 28V, I_B = 0$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			1.0	V	$I_C = 100mA, I_B = 20mA$
Collector-Emitter Sustaining Voltage	$V_{(BR)CER(sus)}$	55			V	$I_C = 5mA, R_{BE} = 10\Omega$
Static Forward Current Transfer	h_{FE}	15		200		$I_C = 50mA, V_{CE} = 5V$
Transitional Frequency	f_T	400	700		MHz	$I_C = 25mA, V_{CE} = 15V, f = 100MHz$
Output Capacitance	C_{obo}			3.0	pF	$V_{CB} = 30V, I_E = 0, f = 1MHz$
R.F. Power Output	P_{OUT}	700	900		mW	$V_{CC} = 28V, P_{IN} = 100mW, f = 400MHz$
Efficiency	η	50	70		%	

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